

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



NIKO-SEM

N- & P-Channel Enhancement Mode
Field Effect Transistor

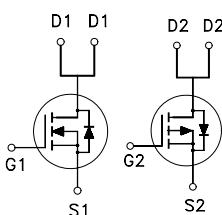
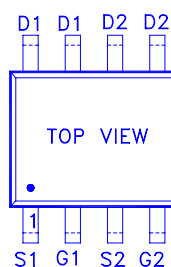
P2503NVG

SOP-8

Lead-Free

PRODUCT SUMMARY

	$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
N-Channel	30	25m Ω	7A
P-Channel	-30	45m Ω	-5A

G : GATE
D : DRAIN
S : SOURCEABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	N-Channel	P-Channel	UNITS
Drain-Source Voltage		V _{DS}	30	-30	V
Gate-Source Voltage		V _{GS}	±20	±20	V
Continuous Drain Current	T _C = 25 °C	I _D	7	-5	A
	T _C = 70 °C		6	-4	
Pulsed Drain Current ¹		I _{DM}	20	-20	
Power Dissipation	T _C = 25 °C	P _D	2		W
	T _C = 70 °C		1.3		
Junction & Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	$^\circ\text{C} / \text{W}$

¹Pulse width limited by maximum junction temperature.²Duty cycle $\leq 1\%$ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT	
			MIN	TYP	MAX		
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	N-Ch	30			V
		$V_{GS} = 0V, I_D = -250\mu A$	P-Ch	-30			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	N-Ch	1	1.5	2.5	
		$V_{DS} = V_{GS}, I_D = -250\mu A$	P-Ch	-1	-1.5	-2.5	

Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	N-Ch			± 100	nA
		$V_{DS} = 0V, V_{GS} = \pm 20V$	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$	N-Ch			1	μA
		$V_{DS} = -24V, V_{GS} = 0V$	P-Ch			-1	
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 55^\circ C$	N-Ch			10	
		$V_{DS} = -20V, V_{GS} = 0V, T_J = 55^\circ C$	P-Ch			-10	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 5V, V_{GS} = 10V$	N-Ch	20			A
		$V_{DS} = -5V, V_{GS} = -10V$	P-Ch	-20			
Drain-Source Resistance ¹ On-State	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 6A$	N-Ch		25	37	m Ω
		$V_{GS} = -4.5V, I_D = -4A$	P-Ch		58	80	
		$V_{GS} = 10V, I_D = 7A$	N-Ch		18	25	
		$V_{GS} = -10V, I_D = -5A$	P-Ch		34	45	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 7A$	N-Ch		19		S
		$V_{DS} = -5V, I_D = -5A$	P-Ch		11		

DYNAMIC

Input Capacitance	C_{iss}	N-Channel	N-Ch		790		pF
		P-Channel	P-Ch		690		
Output Capacitance	C_{oss}	$V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$	N-Ch		175		
		P-Channel	P-Ch		310		
Reverse Transfer Capacitance	C_{rss}	$V_{GS} = 0V, V_{DS} = -10V, f = 1MHz$	N-Ch		65		pF
			P-Ch		75		
Total Gate Charge ²	Q_g	N-Channel	N-Ch		16		nC
		$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = 10V,$	P-Ch		14		
		$I_D = 7A$	N-Ch		2.5		
Gate-Source Charge ²	Q_{gs}	P-Channel	P-Ch		2.2		
		$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = -10V,$	N-Ch		2.1		
Gate-Drain Charge ²	Q_{gd}	$I_D = -5A$	P-Ch		1.9		

Turn-On Delay Time ²	t _{d(on)}	N-Channel V _{DD} = 10V I _D ≅ 1A, V _{GS} = 10V, R _{GEN} = 6 Ω P-Channel V _{DD} = -10V I _D ≅ -1A, V _{GS} = -10V, R _{GEN} = 6 Ω	N-Ch		2.2	4.4	nS
			P-Ch		6.7	13.4	
Rise Time ²	t _r		N-Ch		7.5	15	
			P-Ch		9.7	19.4	
Turn-Off Delay Time ²	t _{d(off)}		N-Ch		11.8	21.3	
			P-Ch		19.8	35.6	
Fall Time ²	t _f		N-Ch		3.7	7.4	
			P-Ch		12.3	22.2	
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T _c = 25 °C)							
Continuous Current	I _S		N-Ch			1.3	A
			P-Ch			-1.3	
Pulsed Current ³	I _{SM}		N-Ch			2.6	
			P-Ch			-2.6	
Forward Voltage ¹	V _{SD}	I _F = 1A, V _{GS} = 0V	N-Ch			1	V
		I _F = -1A, V _{GS} = 0V	P-Ch			-1	

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

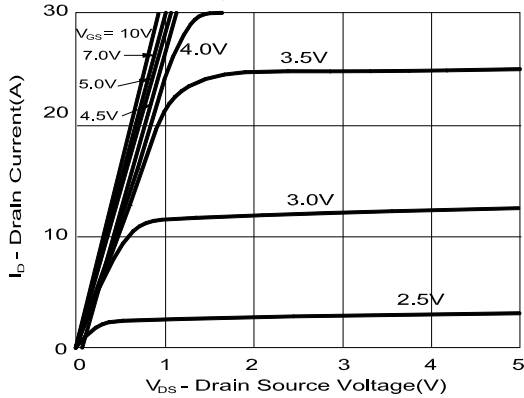
³Pulse width limited by maximum junction temperature.

REMARK: THE PRODUCT MARKED WITH "P2503NVG", DATE CODE or LOT #

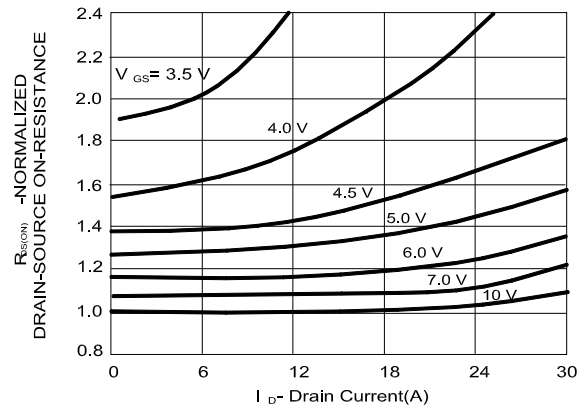
Orders for parts with Lead-Free plating can be placed using the PXXXXXXG parts name.

N-CHANNEL

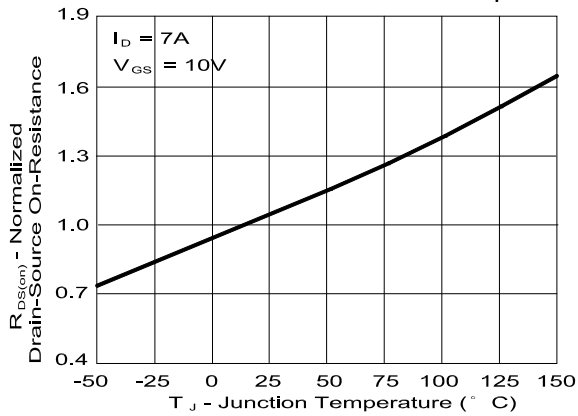
On-Region Characteristics



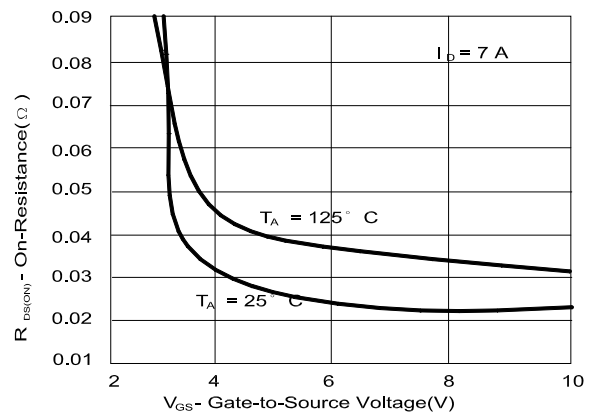
On-Resistance Variation with Drain Current and Gate Voltage



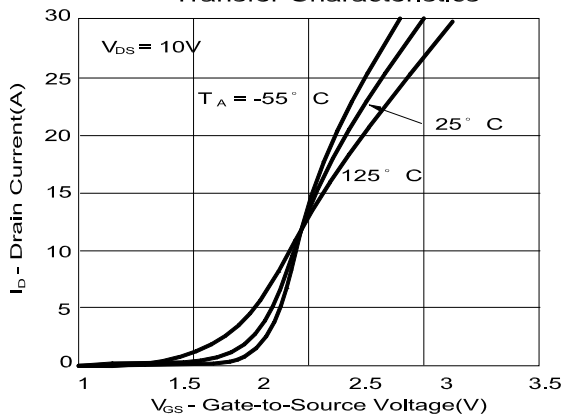
On-Resistance Variation with Temperature



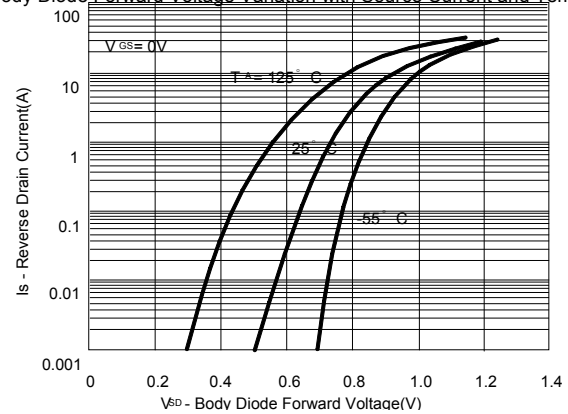
On-Resistance Variation with Gate-to-Source Voltage

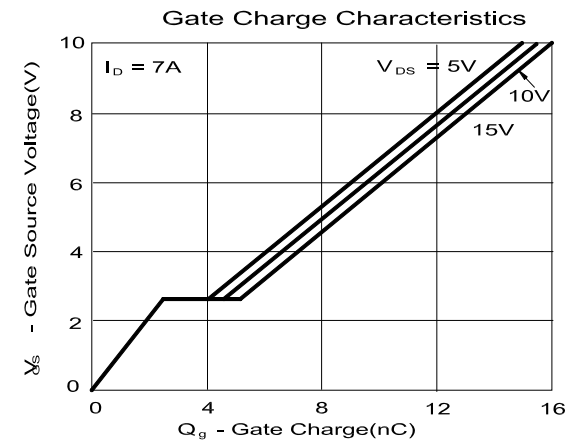
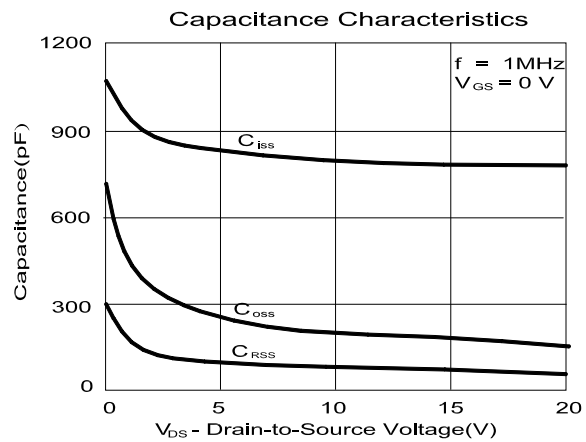
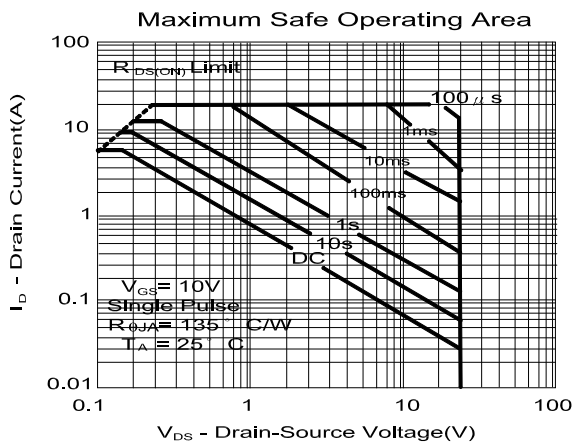
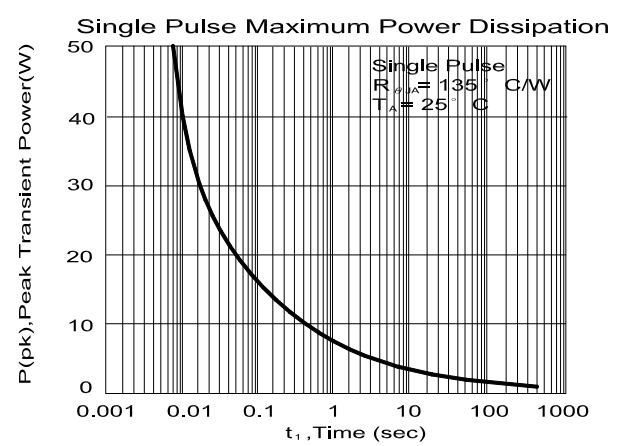


Transfer Characteristics



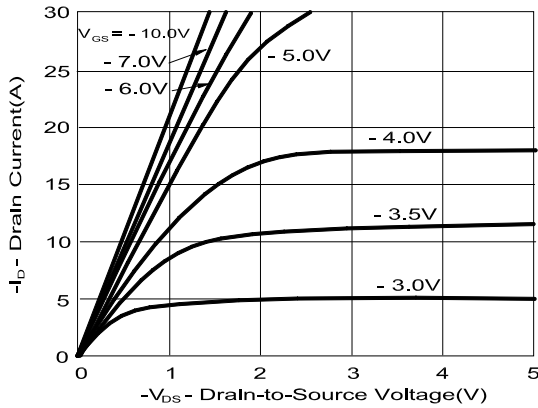
Body Diode Forward Voltage Variation with Source Current and Temperature



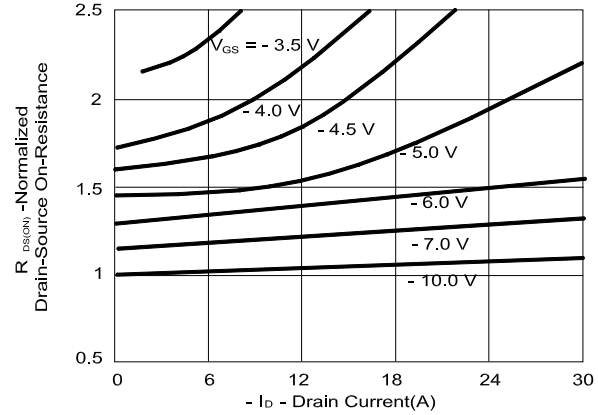


P-CHANNEL

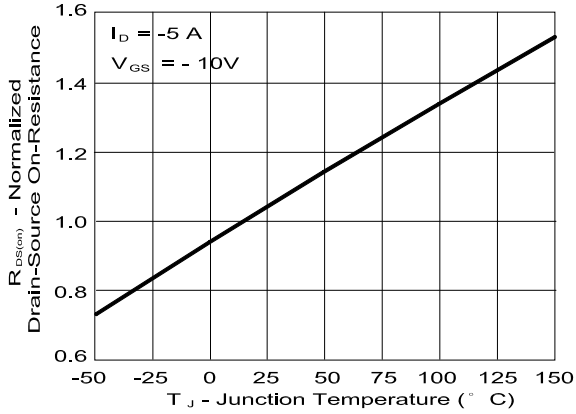
On-Region Characteristics



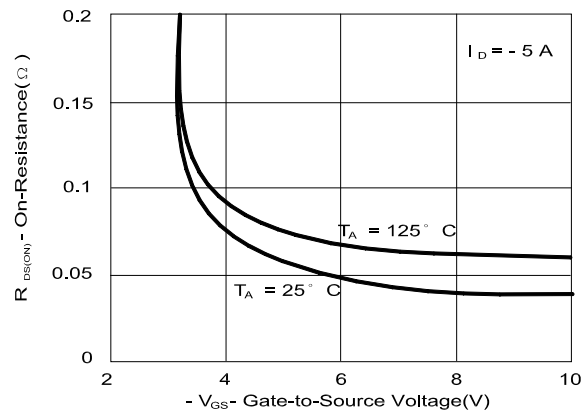
On-Resistance Variation with Drain Current and Gate Voltage



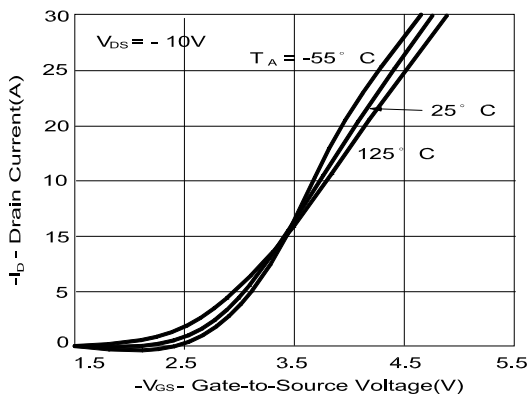
On-Resistance Variation with Temperature



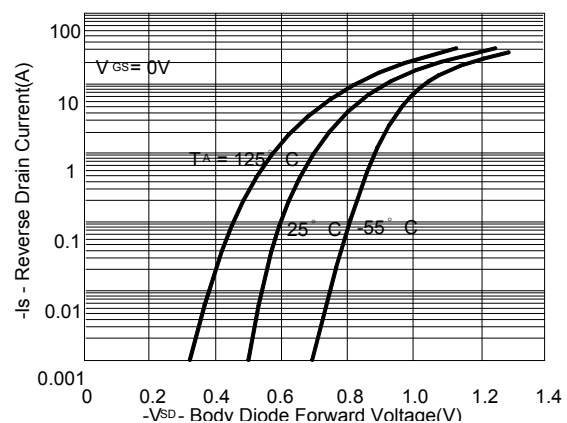
On-Resistance Variation with Gate-to-Source Voltage

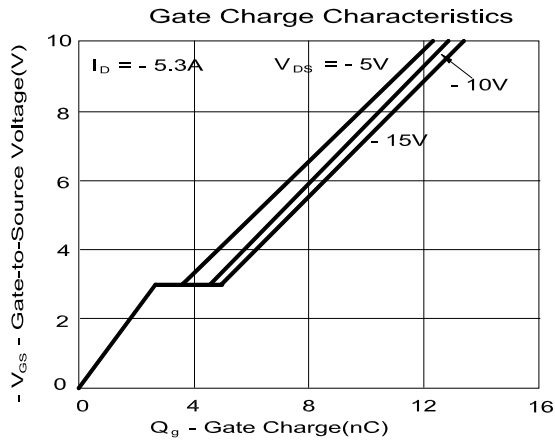
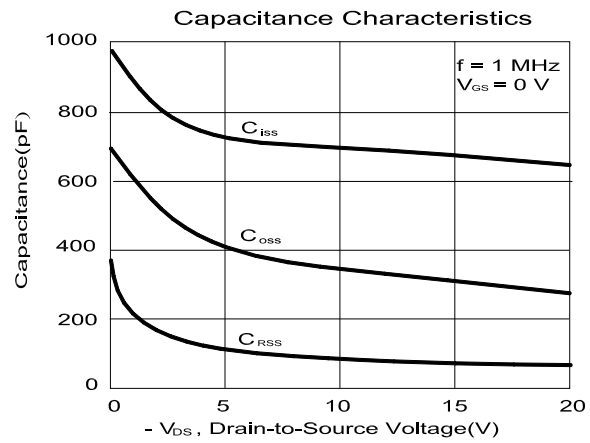
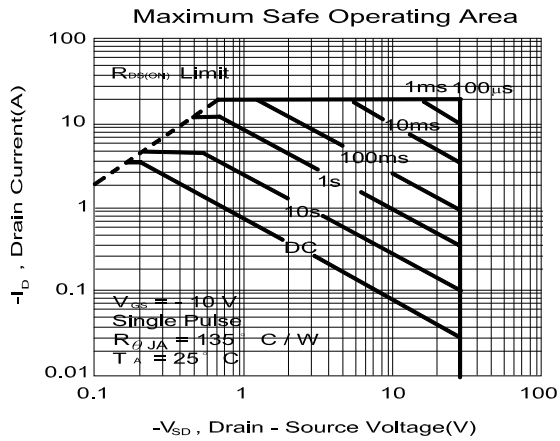
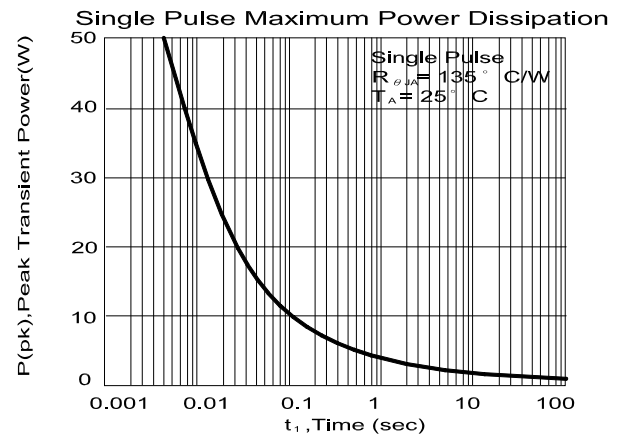
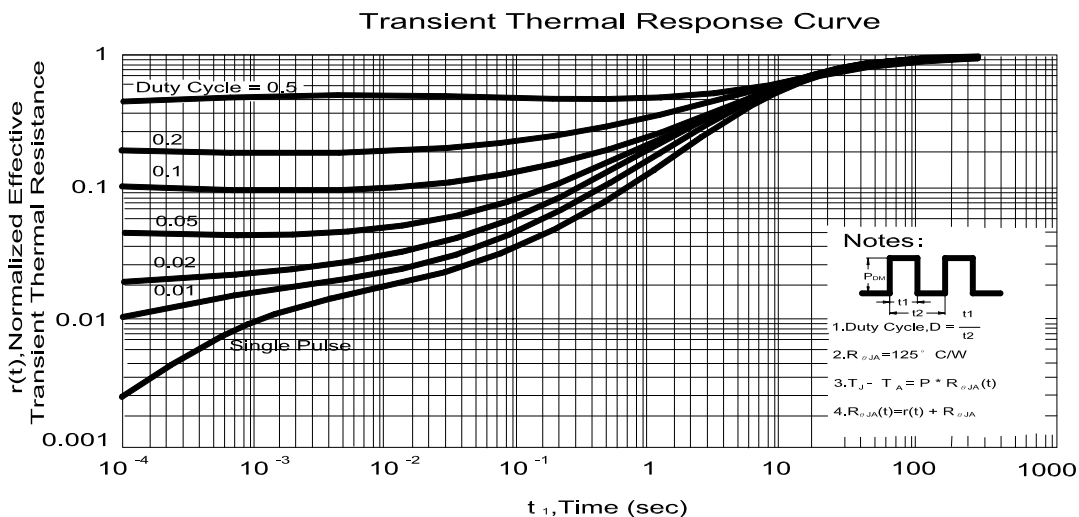


Transfer Characteristics



Body Diode Forward Voltage Variation with Source Current and Temperature





SOIC-8(D) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.5	0.715	0.83
B	3.8	3.9	4.0	I	0.18	0.254	0.25
C	5.8	6.0	6.2	J		0.22	
D	0.38	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.35	1.55	1.75	M			
G	0.1	0.175	0.25	N			

